



isc Silicon NPN Power Transistor

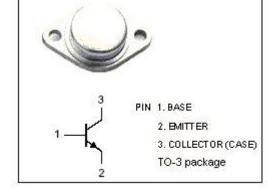
DESCRIPTION

- · High Collector-Emitter Sustaining Voltage-
- : V_{CEO(SUS)}= 400V (Min)
- High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- · Power switching
- Power amplification
- Power driver



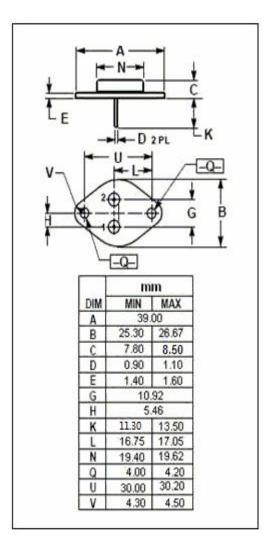


ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | MAX | UNIT |
|------------------|--|---------|--------------|
| V _{CBO} | Collector-Base Voltage | 450 | V |
| Vceo | Collector-Emitter Voltage | 400 | V |
| V _{EBO} | Emitter-Base Voltage | 5 | V |
| Ic | Collector Current-Continuous | 5 | Α |
| Ісм | Collector Current-Peak | 10 | Α |
| I _B | Base Current-Continuous | 2 | Α |
| Pc | Collector Power Dissipation @T _C =25°C | 100 | W |
| Tj | Junction Temperature | 200 | $^{\circ}$ |
| T _{stg} | Storage Temperature Range | -65~200 | $^{\circ}$ C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|-------------------------------------|-----|------|
| R _{th j-c} | Thermal Resistance,Junction to Case | 1.0 | °C/W |





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2SC2243

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| T _C =25°C unless otherwise specified | | | | | | | | | |
|---|--------------------------------------|--|-----|------|------------|------------|--|--|--|
| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT | | | |
| V _{CEO(SUS)} | Collector-Emitter Sustainig Voltage | I _C = 50mA; L= 25mH | 400 | | | V | | | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 2A; I _B = 0.4A | | | 1.2 | V | | | |
| V _{BE} (sat) | Base-Emitter Saturation Voltage | I _C = 2A; I _B = 0.4A | | | 1.5 | V | | | |
| h _{FE} | DC Current Gain | I _C = 2A; V _{CE} = 5V | 10 | | | | | | |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 450V; I _E = 0 T _C =125℃ | | | 1.0 4.0 | mA | | | |
| I _{CEO} | Collector Cutoff Current | V _{CE} = 400V; I _B = 0 | | | 5.0 | mA | | | |
| ІЕВО | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 1.0 | mA | | | |
| Switching Times | | | | | | | | | |
| tr | Rise Time | | | | 1.0 | μ S | | | |
| t _{stg} | Storage Time | I _C =2A; I _{B1} =- I _{B2} = 0.4A | | | 2.0 | μ \$ | | | |
| t _f | Fall Time | | | | 1.0 | μ S | | | |

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